

## -40V P-Channel Enhancement Mode MOSFET

## Description

The SX12P04S uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

 $V_{DS} = -40V I_{D} = -12A$ 

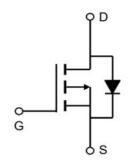
 $R_{DS(ON)}$  < 18m $\Omega$  @ V<sub>GS</sub>=-10V

## **Application**

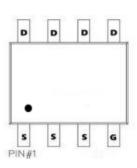
Battery protection

Load switch

Uninterruptible power supply







Absolute Maximum Ratings (TC=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
Vps	Drain-Source Voltage	-40	V
Vgs	Gate-Source Voltage ±20		V
lo@Tc=25℃	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	-12	Α
lo@Tc=75℃	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	-8.9	Α
Ірм	Pulsed Drain Current <sup>2</sup>	-36	Α
EAS	Single Pulse Avalanche Energy <sup>3</sup>	125	mJ
Pb@Tc=25℃	Total Power Dissipation <sup>4</sup>	3.5	W
Pb@Ta=25°C	Total Power Dissipation <sup>4</sup>	1.9	W
Тѕтс	Storage Temperature Range	-55 to 150	$^{\circ}$ C
TJ	Operating Junction Temperature Range	-55 to 150	$^{\circ}$ C
Reja	Thermal Resistance Junction-Ambient <sup>1</sup>	85	°C/W
Rejc	Thermal Resistance Junction-Case <sup>1</sup>	5 °C/W	





## Electrical Characteristics (T<sub>J</sub>=25℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BVDSS	Drain-Source Breakdown Voltage	Vgs=0V , In=-250uA	-40	-44		V	
△BVɒss/△T	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =-1mA		-0.023		V/°C	
	Static Drain-Source On-Resistance <sup>2</sup>	Vgs=-10V , ID=-30A		14	18	mΩ	
RDS(ON)		V <sub>G</sub> s=-4.5V , I <sub>D</sub> =-20A		18	25		
V <sub>GS(th)</sub>	Gate Threshold Voltage	\/ \/   050A	-1.0	-1.6	-2.5	V	
$\triangle V$ GS(th)	V <sub>GS(th)</sub> Temperature Coefficient	Vgs=Vbs , Ib=-250uA		4.74		mV/℃	
	I <sub>DSS</sub> Drain-Source Leakage Current V <sub>DS</sub> =-40V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C V <sub>DS</sub> =-40V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			1	uA		
IDSS		V <sub>DS</sub> =-40V , V <sub>GS</sub> =0V , T <sub>J</sub> =55℃			5	uA	
lgss	Gate-Source Leakage Current	Vgs=±20V , Vps=0V			±100	nA	
Qg	Total Gate Charge (-4.5V)			25		nC	
Qgs	Gate-Source Charge	V <sub>DS</sub> =-20V , V <sub>GS</sub> =-4.5V , l <sub>D</sub> =-12A		11			
$\mathbf{Q}_{gd}$	Gate-Drain Charge	10-12/		9.5			
Td(on)	Turn-On Delay Time			48		ns	
Tr	Rise Time	VDD =-15V, RL=15Ω		24			
Td(off)	Turn-Off Delay Time	ID =-1A, VGEN =-10V, RG =6Ω		88			
Tf	Fall Time			9.6			
Ciss	Input Capacitance			2760			
Coss	Output Capacitance	V <sub>DS</sub> =-20V , V <sub>GS</sub> =0V , f=1MHz		260		pF	
Crss	Reverse Transfer Capacitance			85			
ls	Continuous Source Current <sup>1,5</sup>	\\a=\\==0\\			-40	Α	
lsм	Pulsed Source Current <sup>2,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			-90	Α	
VsD	Diode Forward Voltage <sup>2</sup>	Vgs=0V , Is=-1A , Tյ=25℃			-1.3	V	

#### Note:

- 1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2 . The data tested by pulsed , pulse width  $\leq 300 \text{us}$  , duty cycle  $\leq 2\%$
- $3\,{\mbox{.}}$  The power dissipation is limited by  $150\,{\mbox{°C}}$  junction temperature
- $4\sqrt{100}$  The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.

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## **Typical Characteristics**

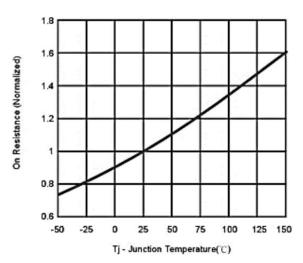
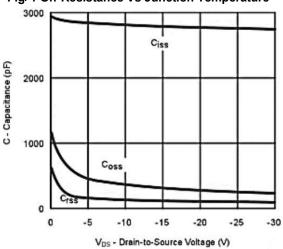


Fig. 1 On Resistance Vs Junction Temperature



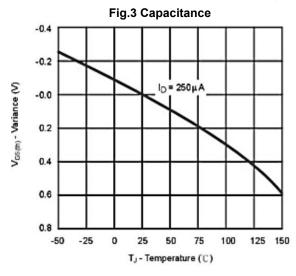


Fig.5 Threshold Voltage

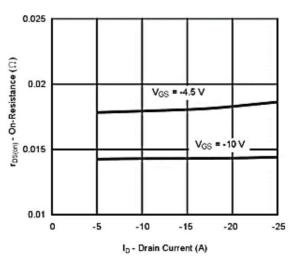


Fig.2 On-Resistance Vs.Drain Current

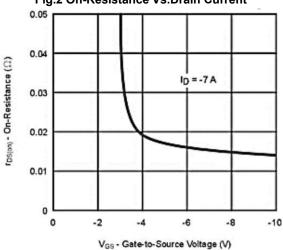


Fig.4 On-Resistance Vs. Gate-to-Sourece Voltage

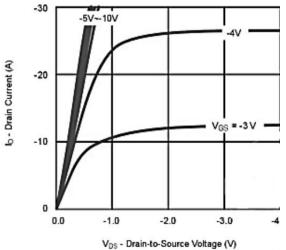


Fig.6 On-Region Characteristics



## **Typical Characteristics**

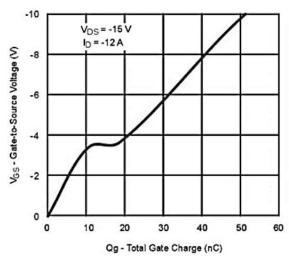


Fig.7 Gate Charge

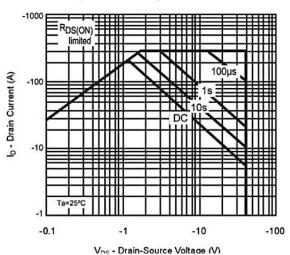


Fig.9 Safe Operating Area

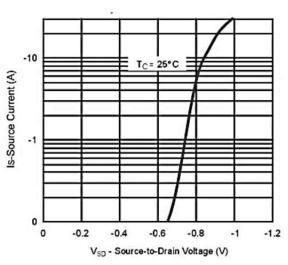


Fig.8 Body-diode Characteristice

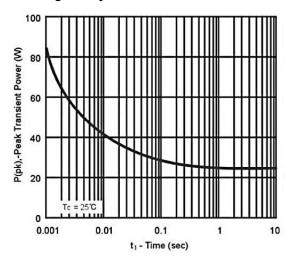


Fig.10 Single Pluse Maximum Power Dissipation

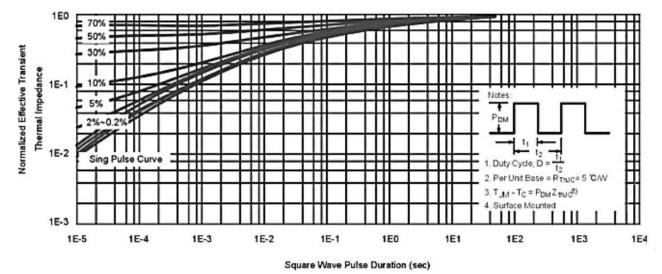
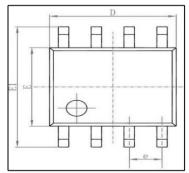


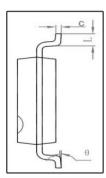
Fig.11 Normalized Maximum Transient Thermal Impedance

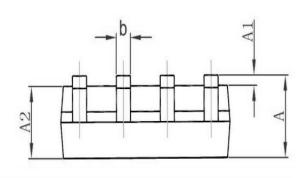




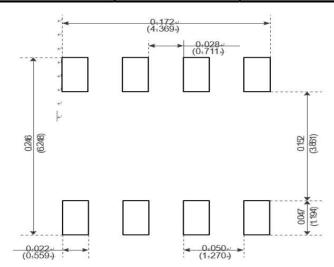
# Package Mechanical Data-SOP-8L







CL. 1	Dimensions In	n Millimeters	Dimensions	In Inches
Symbol	Min	Max	Min	Max
Α	1. 350	1. 750	0. 053	0.069
A1	0. 100	0. 250	0.004	0.010
A2	1. 350	1. 550	0. 053	0.061
b	0. 330	0. 510	0. 013	0. 020
С	0. 170	0. 250	0.006	0. 010
D	4. 700	5. 100	0. 185	0. 200
E	3. 800	4. 000	0. 150	0. 157
E1	5. 800	6. 200	0. 228	0. 244
е	1. 270	(BSC)	0.050	(BSC)
L	0. 400	1. 270	0. 016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads-

# **Package Marking and Ordering Information**

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Product ID	Pack	Marking	Qty(PCS)		
TAPING	SOP-8L		3000		

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